

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

2SD1685 — NPN Epitaxial Planar Silicon Transistor 20V/5A Switching Applications

Applications

· Strobe, voltage regulators, relay drivers, lamp drivers

Features

- · Low saturation voltage
- · Large current capacity
- · Fast switching time
- · No insulator required when mounting because the leadframe of the chip is covered with plastic

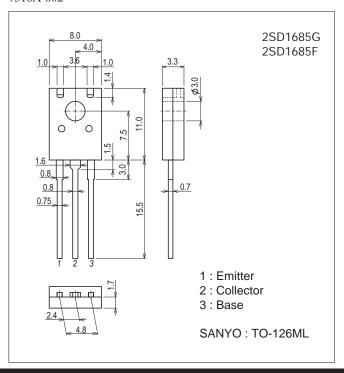
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		60	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	V _{EBO}		6	V
Collector Current	IC		5	Α
Collector Current (Pulse)	ICP		8	Α
Callagter Dissination	Da		1.5	W
Collector Dissipation	PC	Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7516A-002



Product & Package Information

Package : TO-126ML
 JEITA, JEDEC : TO-126
 Minimum Packing Quantity : 200 pcs./bag

Marking



Electrical Connection

3 0 1

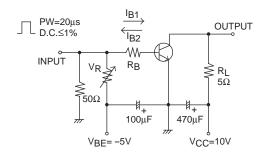
Electrical Characteristics at Ta=25°C

Darameter	Cumbal	Canditions		Linit			
Parameter	Symbol Conditions		min	typ	max	Unit	
Collector Cutoff Current	ICBO	VCB=50V, IE=0A			100	nA	
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0A			100	nA	
DC Current Gain	h _{FE} 1	V _{CE} =2V, I _C =500mA	120*		560*		
DC Current Gain	h _{FE} 2	V _{CE} =2V, I _C =3A	95				
Gain-Bandwidth Product	fŢ	VCE=10V, IC=50mA		120		MHz	
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		45		pF	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =3A, I _B =60mA		220	500	mV	
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =3A, I _B =60mA			1.5	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	60			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	20			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6			V	
Turn-ON Time	ton			30		ns	
Storage Time t _{Stq}		See specified Test Circuit.		300		ns	
Fall Time	tf			40		ns	

* : The 2SD1685 is classified by 500mA hFE as follows :

Rank	Е	F	G	
hFE	120 to 200	160 to 320	280 to 560	

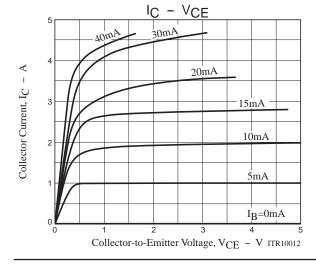
Switching Time Test Circuit

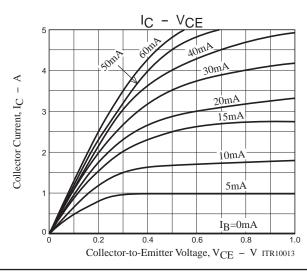


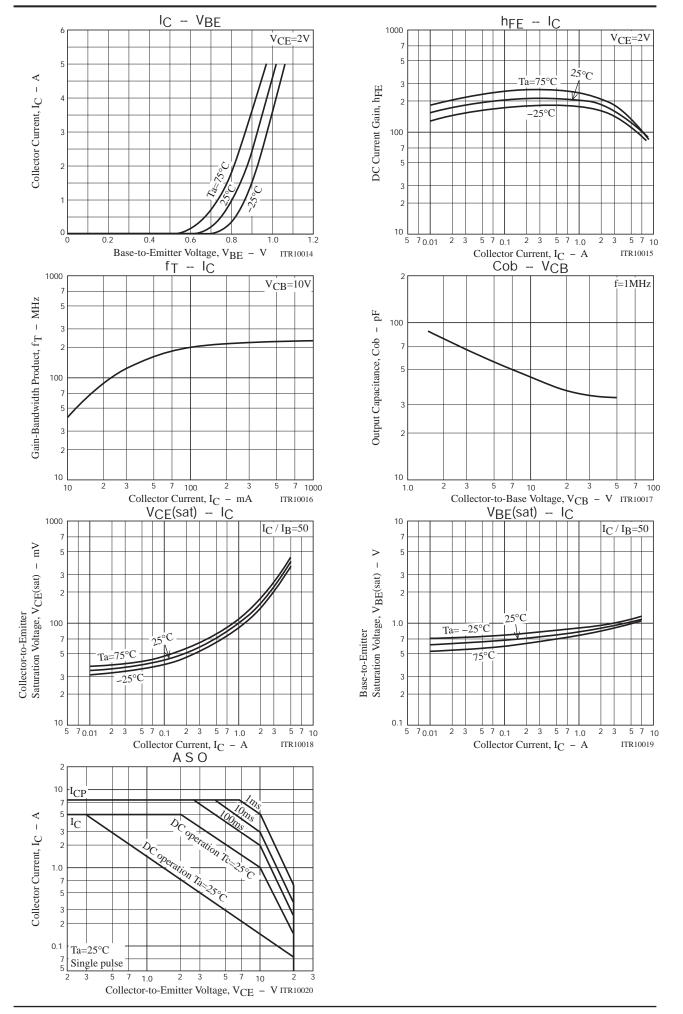
 $I_{C}=10I_{B1}=-10I_{B2}=2A$

Ordering Information

Device	Package Shipping		memo	
2SD1685G	TO-126ML	200pcs./bag	Pb Free	
2SD1685F	TO-126ML	200pcs./bag	Pb Fiee	





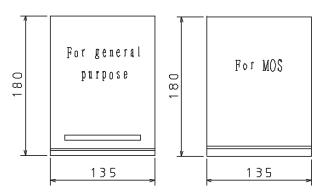


Bag Packing Specification 2SD1685G, 2SD1685F

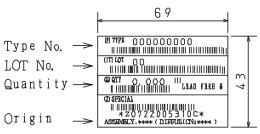
1. Packing Format

Packa	ge Name	Maximum Number of devices contained (pcs) Bag Inner box Cuter box			Packing format		
15185	0.11.2.2.			Quier box	Inner BOX	Outer BOX	
T0-	126ML	200	4,000			A-2 3 inner boxes contained Dimensions:mm (external) 470×250×190	

2. Bag dimensions (unit;mm)



3. Bag label, [nner box label (unit:mm)

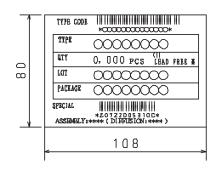


NOTE(1)
The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Labe1		JEITA Phase
LEAD FREE	3	JEITA Phase 3A
LEAD FREE	4	JEITA Phase 3

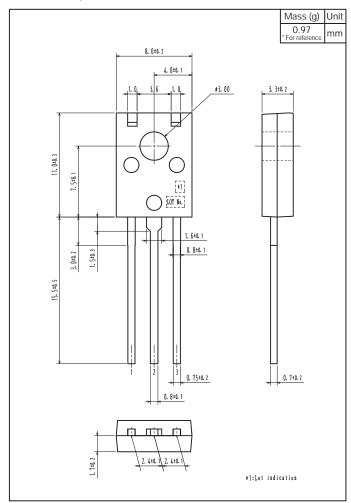
<u>4. Outer box label</u> (unìt:mm)

It is a label at the time of factory shipments, The form of a label may change in physical distribution process.



Outline Drawing

2SD1685G, 2SD1685F



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